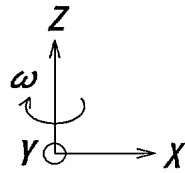
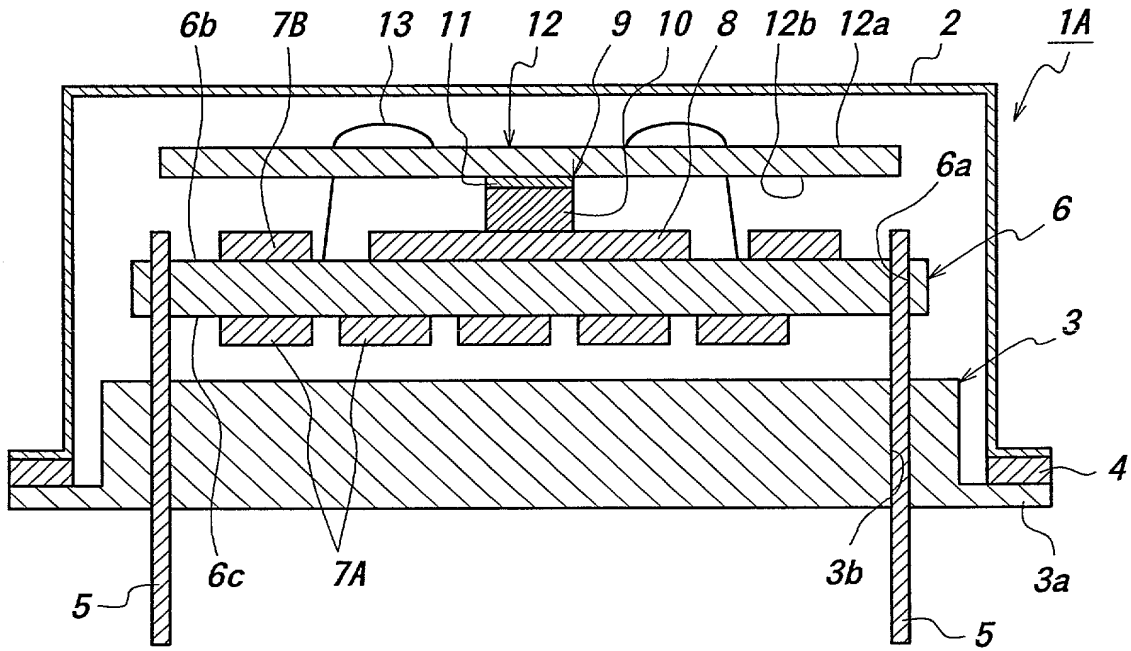


FIG. 1



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FIG. 3

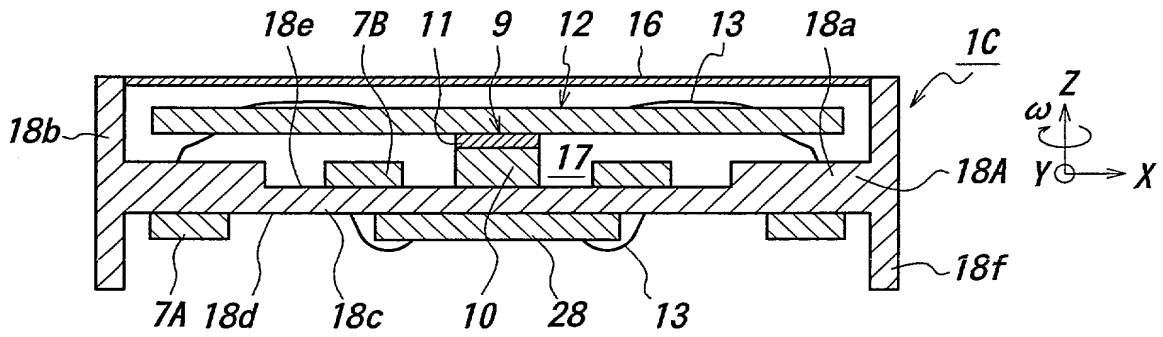


FIG. 4

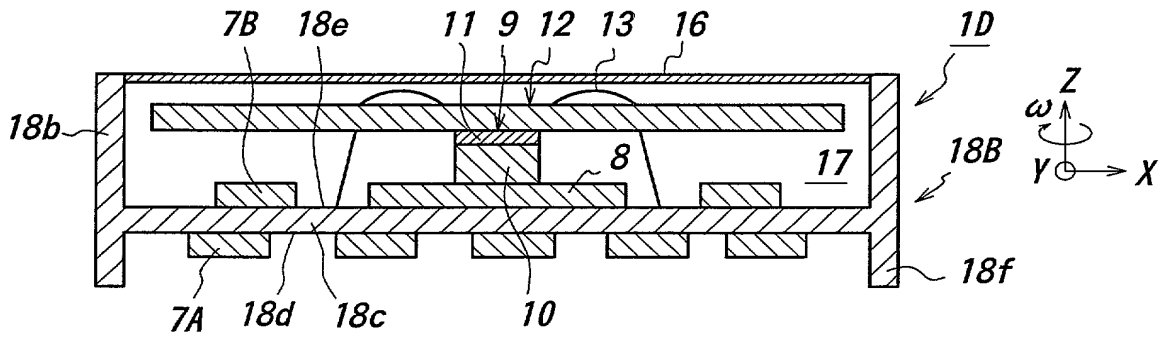


FIG. 5

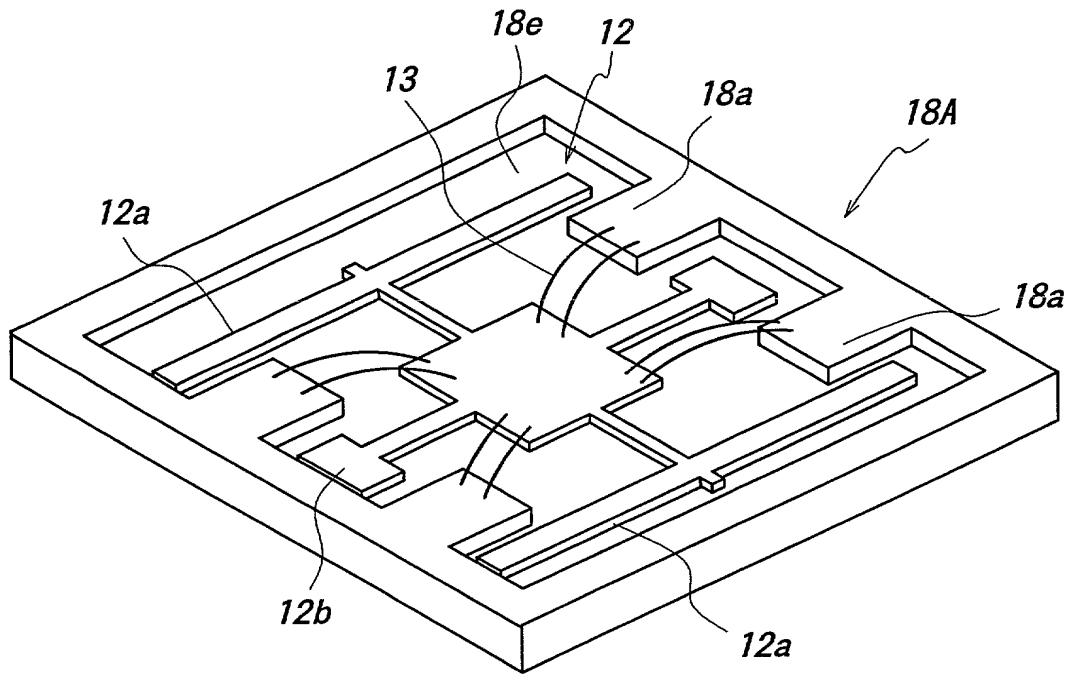


FIG. 7

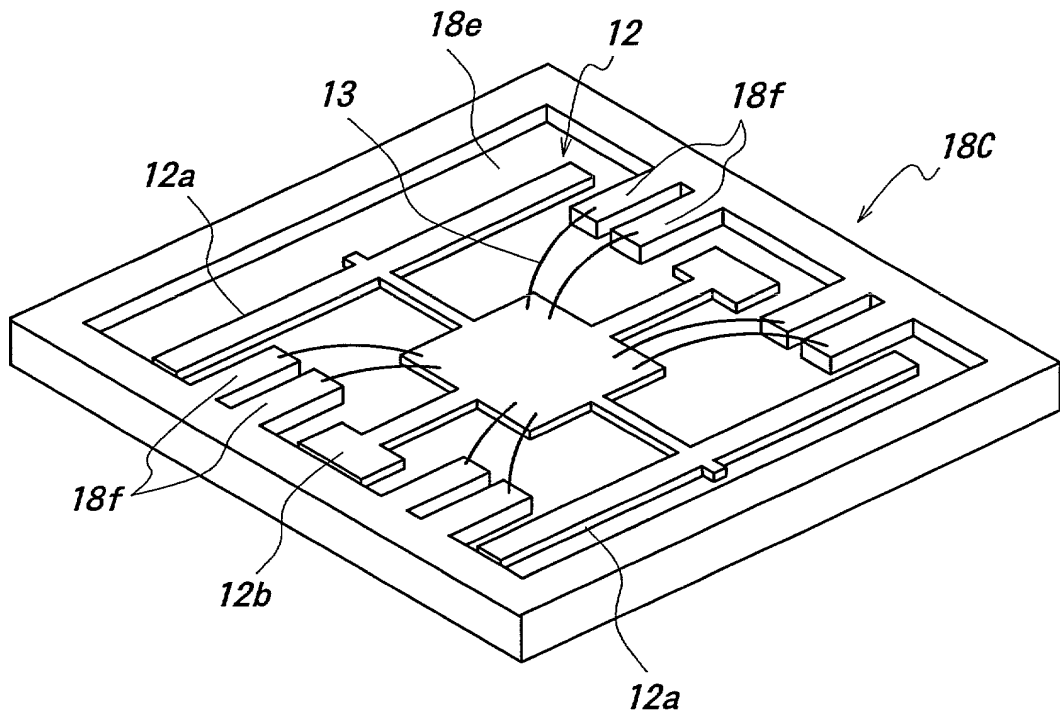


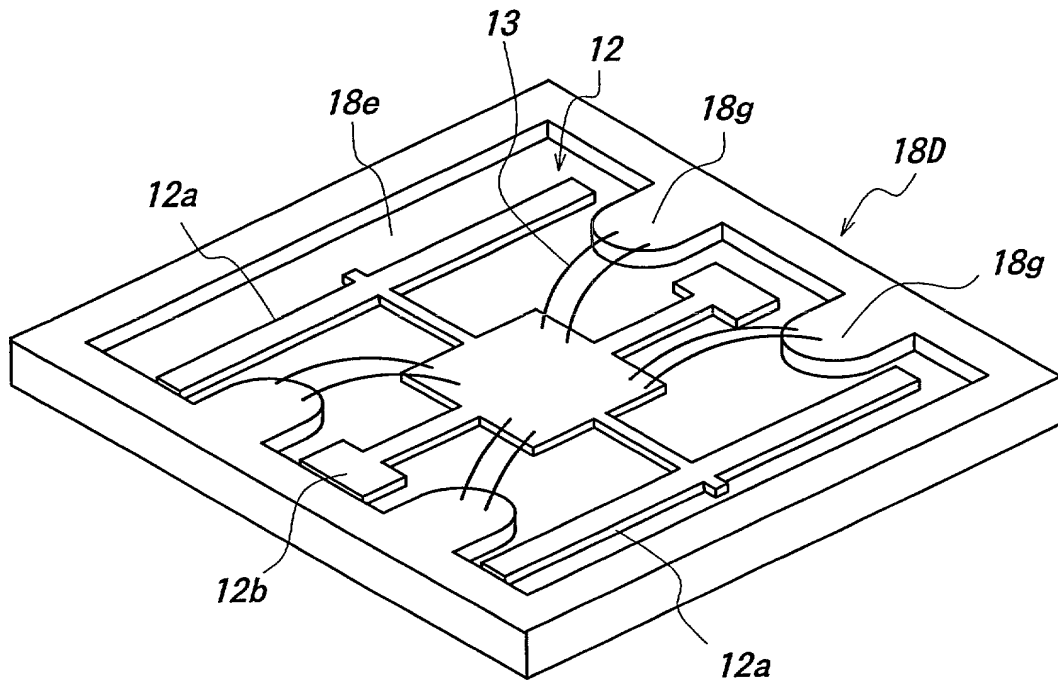
FIG. 8

FIG. 9

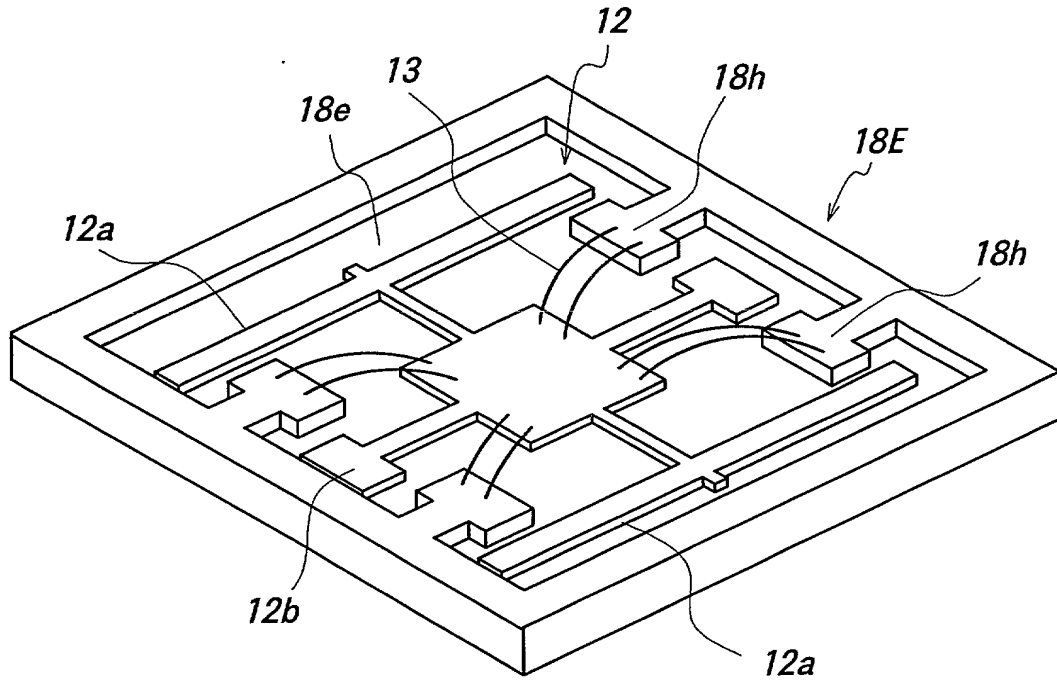
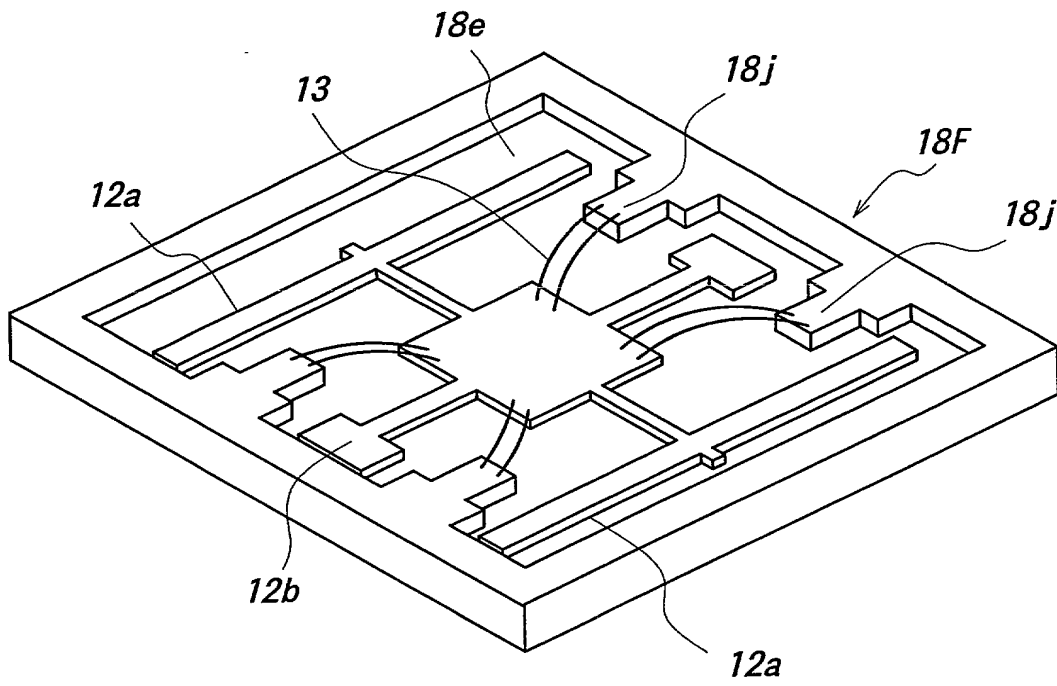


FIG. 9

FIG. 10



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Figure 1E is a cross-sectional view of a semiconductor device. It shows a substrate 3 with a base layer 4, a first conductive layer 5, and a second conductive layer 6. The device includes a central region 8 with a gate structure 11 and 12, and side regions 7A and 7B. Various layers and structures are labeled with numbers 1 through 13.